

# Yvon Cordier

## List of Publications by Year in descending order

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224  
papers

3,625  
citations

159585

30  
h-index

223800

46  
g-index

226  
all docs

226  
docs citations

226  
times ranked

2833  
citing authors

#	ARTICLE	IF	CITATIONS
1	Combination of selective area sublimation of p-GaN and regrowth of AlGa <sub>N</sub> for the co-integration of enhancement mode and depletion mode high electron mobility transistors. Solid-State Electronics, 2022, 188, 108210.	1.4	5
2	Transport characteristics of AlGa <sub>N</sub> /Ga <sub>N</sub> structures for amplification of terahertz radiations. Applied Physics A: Materials Science and Processing, 2022, 128, 1.	2.3	0
3	Micro-Raman characterization of homo-epitaxial n doped Ga <sub>N</sub> layers for vertical device applications. AIP Advances, 2022, 12, 025126.	1.3	4
4	Temperature and Gate-Length Dependence of Subthreshold RF Detection in Ga <sub>N</sub> HEMTs. Sensors, 2022, 22, 1515.	3.8	5
5	Transport properties of a thin Ga <sub>N</sub> channel formed in an Al <sub>0.9</sub> Ga <sub>0.1</sub> N/Ga <sub>N</sub> heterostructure grown on AlN/sapphire template. Journal of Applied Physics, 2022, 131, 124501.	2.5	2
6	A 5.7 THz Ga <sub>N</sub> /AlGa <sub>N</sub> quantum cascade detector based on polar step quantum wells. Applied Physics Letters, 2022, 120, .	3.3	4
7	Selective sublimation of Ga <sub>N</sub> and regrowth of AlGa <sub>N</sub> to co-integrate enhancement mode and depletion mode high electron mobility transistors. Journal of Crystal Growth, 2022, , 126779.	1.5	0
8	AlGa <sub>N</sub> Channel High Electron Mobility Transistors with Regrown Ohmic Contacts. Electronics (Switzerland), 2021, 10, 635.	3.1	27
9	Characterization of m-Ga <sub>N</sub> and a-Ga <sub>N</sub> Crystallographic Planes after Being Chemically Etched in TMAH Solution. Energies, 2021, 14, 4241.	3.1	12
10	New barrier layer design for the fabrication of gallium nitride-metal-insulator-semiconductor-high electron mobility transistor normally-off transistor. Semiconductor Science and Technology, 2021, 36, 034002.	2.0	2
11	Stability of the threshold voltage in fluorine-implanted normally-off AlN/Ga <sub>N</sub> HEMTs co-integrated with commercial normally-on Ga <sub>N</sub> HEMT technology. Microelectronics Reliability, 2021, 126, 114291.	1.7	6
12	Selective Ga <sub>N</sub> sublimation and local area regrowth for co-integration of enhancement mode and depletion mode Al(Ga)N/Ga <sub>N</sub> high electron mobility transistors. Semiconductor Science and Technology, 2021, 36, 024001.	2.0	3
13	Nanoscale structural and electrical properties of graphene grown on AlGa <sub>N</sub> by catalyst-free chemical vapor deposition. Nanotechnology, 2021, 32, 015705.	2.6	6
14	Metalorganic Chemical Vapor Phase Epitaxy Growth of Buffer Layers on 3C-SiC/Si(111) Templates for AlGa <sub>N</sub> /Ga <sub>N</sub> High Electron Mobility Transistors with Low RF Losses. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900760.	1.8	8
15	Cathodoluminescence and electrical study of vertical Ga <sub>N</sub> -on-Ga <sub>N</sub> Schottky diodes with dislocation clusters. Journal of Crystal Growth, 2020, 552, 125911.	1.5	4
16	Electrical activity at the AlN/Si Interface: identifying the main origin of propagation losses in Ga <sub>N</sub> -on-Si devices at microwave frequencies. Scientific Reports, 2020, 10, 14166.	3.3	20
17	AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors on diamond substrate obtained through aluminum nitride bonding technology. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, .	1.2	7
18	Trapping Dipolar Exciton Fluids in Ga <sub>N</sub> /(AlGa)N Nanostructures. Nano Letters, 2019, 19, 4911-4918.	9.1	9

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19	High Lateral Breakdown Voltage in Thin Channel AlGaIn/GaN High Electron Mobility Transistors on AlN/Sapphire Templates. <i>Micromachines</i> , 2019, 10, 690.	2.9	28
20	High-Performance Graphene/AlGaIn/GaN Schottky Junctions for Hot Electron Transistors. <i>ACS Applied Electronic Materials</i> , 2019, 1, 2342-2354.	4.3	35
21	2 W mm <sup>-2</sup> power density of an AlGaIn/GaN HEMT grown on free-standing GaN substrate at 40 GHz. <i>Semiconductor Science and Technology</i> , 2019, 34, 12LT01.	2.0	10
22	Kapitza thermal resistance characterization of epitaxial graphene/SiC(0001) interface. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	6
23	Structural and electrical properties of AlN thin films on GaN substrates grown by plasma enhanced-Atomic Layer Deposition. <i>Materials Science in Semiconductor Processing</i> , 2019, 97, 35-39.	4.0	11
24	Terahertz intersubband absorption of GaN/AlGaIn step quantum wells grown by MOVPE on Si(111) and Si(110) substrates. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	6
25	Buried defects induced by plasma assisted molecular beam epitaxy of AlN and GaN on Silicon. <i>Journal of Crystal Growth</i> , 2019, 507, 220-225.	1.5	2
26	Crack Statistics and Stress Analysis of Thick GaN on Patterned Silicon Substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700399.	1.5	3
27	Influence of AlN Growth Temperature on the Electrical Properties of Buffer Layers for GaN HEMTs on Silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700637.	1.8	22
28	AlGaIn/GaN/AlGaIn DH-HEMTs Grown on a Patterned Silicon Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700642.	1.8	6
29	Optical and Thermal Performances of (Ga,In)N/GaN Light Emitting Diodes Transferred on a Flexible Tape. <i>IEEE Photonics Technology Letters</i> , 2018, 30, 1567-1570.	2.5	4
30	A comparative study of graphene growth on SiC by hydrogen-CVD or Si sublimation through thermodynamic simulations. <i>CrystEngComm</i> , 2018, 20, 3702-3710.	2.6	8
31	Hot Electron Transistors with Graphene Base for THz Electronics. , 2018, , 95-115.		2
32	High temperature annealing and CVD growth of few-layer graphene on bulk AlN and AlN templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600436.	1.8	10
33	Recent improvements of flexible GaN-based HEMT technology. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600484.	1.8	18
34	Anomalous DC and RF behavior of virgin AlGaIn/AlN/GaN HEMTs. <i>Semiconductor Science and Technology</i> , 2017, 32, 035011.	2.0	9
35	Trap states analysis in AlGaIn/AlN/GaN and InAlN/AlN/GaN high electron mobility transistors. <i>Current Applied Physics</i> , 2017, 17, 1601-1608.	2.4	13
36	Influence of metal-organic vapor phase epitaxy parameters and Si(111) substrate type on the properties of AlGaIn/GaN HEMTs with thin simple buffer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600419.	1.8	5

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37	Graphene integration with nitride semiconductors for high power and high frequency electronics. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600460.	1.8	38
38	A combined growth process for state-of-the-art GaN on silicon. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600449.	1.8	4
39	Homoepitaxy of non-polar ZnO/(Zn,Mg)O multi-quantum wells: From a precise growth control to the observation of intersubband transitions. Applied Physics Letters, 2017, 111, .	3.3	32
40	Characterization and modeling of traps and RF frequency dispersion in AlGaIn/AlN/GaN HEMTs. , 2016, , .		0
41	Piezoelectric MEMS resonators based on ultrathin epitaxial GaN heterostructures on Si. Journal of Micromechanics and Microengineering, 2016, 26, 105015.	2.6	4
42	Impact of the Bending on the Electroluminescence of Flexible InGaIn/GaN Light-Emitting Diodes. IEEE Photonics Technology Letters, 2016, 28, 1661-1664.	2.5	6
43	Development of technological building blocks for the monolithic integration of ammonia-MBE-grown GaN-HEMTs with silicon CMOS. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 917-924.	1.8	1
44	First Power Performance Demonstration of Flexible AlGaIn/GaN High Electron Mobility Transistor. IEEE Electron Device Letters, 2016, 37, 553-555.	3.9	24
45	Two-dimensional dopant profiling of gallium nitride p-n junctions by scanning capacitance microscopy. Nuclear Instruments & Methods in Physics Research B, 2016, 372, 67-71.	1.4	3
46	Room-Temperature AlGaIn/GaN Terahertz Plasmonic Detectors with a Zero-Bias Grating. Journal of Infrared, Millimeter, and Terahertz Waves, 2016, 37, 243-257.	2.2	13
47	GaN films and GaN/AlGaIn quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. Journal of Crystal Growth, 2016, 433, 165-171.	1.5	6
48	Growth of nitride-based light emitting diodes with a high-reflectivity distributed Bragg reflector on mesa-patterned silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2297-2301.	1.8	9
49	Al(Ga)N/GaN high electron mobility transistors on silicon. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1049-1058.	1.8	13
50	Highly resistive epitaxial Mg-doped GdN thin films. Applied Physics Letters, 2015, 106, .	3.3	18
51	Reduction of the thermal budget of AlGaIn/GaN heterostructures grown on silicon: A step towards monolithic integration of GaN-HEMTs with CMOS. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1145-1152.	1.8	5
52	Erratum to "Gallium Nitride as an Electromechanical Material" [Dec 14 1252-1271]. Journal of Microelectromechanical Systems, 2015, 24, 249-249.	2.5	0
53	Nanoscale conductive pattern of the homoepitaxial AlGaIn/GaN transistor. Nanotechnology, 2015, 26, 115203.	2.6	14
54	Power Performance at 40 GHz of AlGaIn/GaN High-Electron Mobility Transistors Grown by Molecular Beam Epitaxy on Si(111) Substrate. IEEE Electron Device Letters, 2015, 36, 303-305.	3.9	55

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55	On the correlation between kink effect and effective mobility in InAlN/GaN HEMTs. , 2014, , .		9
56	Integration of Micro Resistance Thermometer Detectors in AlGaIn/GaN Devices. IEEE Journal of the Electron Devices Society, 2014, 2, 145-148.	2.1	13
57	Gallium Nitride as an Electromechanical Material. Journal of Microelectromechanical Systems, 2014, 23, 1252-1271.	2.5	173
58	Graphene growth on AlN templates on silicon using propane-hydrogen chemical vapor deposition. Applied Physics Letters, 2014, 104, .	3.3	17
59	Magnetic properties of Gd-doped GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 1673-1684.	1.5	13
60	GaN high electron mobility transistors on silicon substrates with MBE/PVD AlN seed layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 498-501.	0.8	4
61	AlGaIn/GaN HEMTs with very thin buffer on Si (111) for nanosystems applications. Semiconductor Science and Technology, 2014, 29, 115018.	2.0	9
62	Molecular beam epitaxy of ferromagnetic epitaxial GdN thin films. Journal of Crystal Growth, 2014, 404, 146-151.	1.5	18
63	Influence of 3C-SiC/Si (111) template properties on the strain relaxation in thick GaN films. Journal of Crystal Growth, 2014, 398, 23-32.	1.5	13
64	Young's modulus extraction of epitaxial heterostructure AlGaIn/GaN for MEMS application. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1655-1659.	1.8	14
65	Magnetotransport in a two-subband AlGaIn/GaN heterostructure in the presence of mixed disorder. EPJ Applied Physics, 2014, 68, 20102.	0.7	1
66	Magnetotransport studies of AlGaIn/GaN heterostructures with two-dimensional electron gas in parallel with a three-dimensional Al-graded layer: Incorrect hole type determination. Journal of Applied Physics, 2013, 114, 023704.	2.5	0
67	Room temperature generation of THz radiation in GaN quantum wells structures. Proceedings of SPIE, 2013, , .	0.8	0
68	Stress distribution of 12 $\mu$ m thick crack free continuous GaN on patterned Si(110) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 425-428.	0.8	12
69	Optimization of $\{m_{Al}\}_{0.29}\{m_{Ga}\}_{0.71}\{m_{N}\}/\{m_{GaN}\}$ High Electron Mobility Heterostructures for High-Power/Frequency Performances. IEEE Transactions on Electron Devices, 2013, 60, 3105-3111.	3.0	22
70	Molecular beam epitaxial AlGaIn/GaN high electron mobility transistors leakage thermal activation on silicon and sapphire. Applied Physics Letters, 2013, 102, .	3.3	4
71	Tuning the electromagnetic local density of states in graphene-covered systems via strong coupling with graphene plasmons. Physical Review B, 2013, 87, .	3.2	56
72	Fabrication, Characterization, and Physical Analysis of AlGaIn/GaN HEMTs on Flexible Substrates. IEEE Transactions on Electron Devices, 2013, 60, 1054-1059.	3.0	19

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73	Power Performance of AlGaIn/GaN High-Electron-Mobility Transistors on (110) Silicon Substrate at 40 GHz. IEEE Electron Device Letters, 2013, 34, 490-492.	3.9	48
74	AlGaIn/GaN HEMTs with an InGaIn back-barrier grown by ammonia-assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 480-483.	1.8	11
75	Analysis of the AlGaIn/GaN vertical bulk current on Si, sapphire, and free-standing GaN substrates. Journal of Applied Physics, 2013, 113, .	2.5	57
76	Assessment of transistors based on GaN on silicon substrate in view of integration with silicon technology. Semiconductor Science and Technology, 2013, 28, 094003.	2.0	9
77	Role of magnetic polarons in ferromagnetic GdN. Physical Review B, 2013, 87, .	3.2	40
78	Gate traps inducing band-bending fluctuations on AlGaIn/GaN heterojunction transistors. Applied Physics Letters, 2013, 102, 023511.	3.3	15
79	Terahertz transmission and effective gain measurement of two-dimensional electron gas. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1454-1458.	1.8	2
80	Delta-Doping of Epitaxial GaN Layers on Large Diameter Si(111) Substrates. Applied Physics Express, 2012, 5, 025504.	2.4	9
81	Temperature impact and analytical modeling of the AlGaIn/GaN-on-Si saturation drain current and transconductance. Semiconductor Science and Technology, 2012, 27, 125010.	2.0	18
82	Effects of substrate orientation on the optical anisotropy spectra of GaN/AlN/Si heterostructures in the energy range from 2.0 to 3.5 eV. Journal of Applied Physics, 2012, 111, .	2.5	6
83	Graphene/SiC Interface Control Using Propane-Hydrogen CVD on 6H-SiC(0001) and 3C-SiC(111)/Si(111). Materials Science Forum, 2012, 711, 253-257.	0.3	4
84	Bias Dependence of Gallium Nitride Micro-Electro-Mechanical Systems Actuation Using a Two-Dimensional Electron Gas. Applied Physics Express, 2012, 5, 067201.	2.4	7
85	Bulk Temperature Impact on the AlGaIn/GaN HEMT Forward Current on Si, Sapphire and Free-Standing GaN. ECS Solid State Letters, 2012, 2, P4-P7.	1.4	10
86	Fabrication and growth of GaN-based micro and nanostructures. International Journal of Nanotechnology, 2012, 9, 412.	0.2	6
87	Effect of carbon doping on crystal quality, electrical isolation and electron trapping in GaN based structures grown silicon substrates. Solid-State Electronics, 2012, 75, 86-92.	1.4	24
88	Gate current analysis of AlGaIn/GaN on silicon heterojunction transistors at the nanoscale. Applied Physics Letters, 2012, 101, 093505.	3.3	18
89	Nanoscale investigation of AlGaIn/GaN-on-Si high electron mobility transistors. Nanotechnology, 2012, 23, 395204.	2.6	13
90	Growth optimization and characterization of lattice-matched Al <sub>0.82</sub> In <sub>0.18</sub> N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	1.5	10

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91	Growth mode and electric properties of graphene and graphitic phase grown by argon-propane assisted CVD on 3C-SiC/Si and 6H-SiC. Journal of Crystal Growth, 2012, 349, 27-35.	1.5	27
92	Reverse current thermal activation of AlGaN/GaN HEMTs on Si(111). Microelectronics Reliability, 2012, 52, 2547-2550.	1.7	3
93	Analysis of the SiO <sub>2</sub> /Si <sub>3</sub> N <sub>4</sub> passivation bilayer thickness on the rectifier behavior of AlGaN/GaN HEMTs on (111) silicon substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1083-1087.	0.8	4
94	Influence of nitrogen precursor and its flow rate on the quality and the residual doping in GaN grown by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 523-526.	0.8	5
95	Electromechanical Transconductance Properties of a GaN MEMS Resonator With Fully Integrated HEMT Transducers. Journal of Microelectromechanical Systems, 2012, 21, 370-378.	2.5	82
96	Voltage-controlled sub-terahertz radiation transmission through GaN quantum well structure. Applied Physics Letters, 2011, 99, 082101.	3.3	13
97	RF Performance of AlGaN/GaN High-Electron-Mobility Transistors Grown on Silicon (110). Applied Physics Express, 2011, 4, 064105.	2.4	17
98	Micro and nano analysis of 0.2 µm Ti/Al/Ni/Au ohmic contact to AlGaN/GaN. Applied Physics Letters, 2011, 99, 213504.	3.3	47
99	Gallium nitride approach for MEMS resonators with highly tunable piezo-amplified transducers. , 2011, , .		1
100	GaN Ohmic contact resistance vs temperature. , 2011, , .		3
101	Effect of surface preparation and interfacial layer on the quality of SiO <sub>2</sub> /GaN interfaces. Journal of Applied Physics, 2011, 109, .	2.5	33
102	Temperature dependence of Al/Ti-based Ohmic contact to GaN devices: HEMT and MOSFET. Microelectronic Engineering, 2011, 88, 3140-3144.	2.4	24
103	Growth of thick, continuous GaN layers on 4-in. Si substrates by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2011, 314, 85-91.	1.5	100
104	Growth of GaN based structures on focused ion beam patterned templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1516-1519.	0.8	2
105	Growth of thick GaN layers on 4-in. and 6-in. silicon (111) by metalorganic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1479-1482.	0.8	42
106	Thermal effects in AlGaN/GaN/Si high electron mobility transistors. Solid-State Electronics, 2011, 61, 1-6.	1.4	26
107	Dyakonov-Perel electron spin relaxation in a wurtzite semiconductor: From the nondegenerate to the highly degenerate regime. Physical Review B, 2011, 84, .	3.2	23
108	GaN: A multifunctional material enabling MEMS resonators based on amplified piezoelectric detection. , 2011, , .		5



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109	Voltage Controlled Terahertz Transmission Enhancement through GaN Quantum Wells. Acta Physica Polonica A, 2011, 119, 107-110.	0.5	1
110	Measurement of Pulsed Current-Voltage Characteristics of AlGaIn/GaN HEMTs from Room Temperature to 15 K. Acta Physica Polonica A, 2011, 119, 196-198.	0.5	4
111	Growth of GaN based structures on Si(110) by molecular beam epitaxy. Journal of Crystal Growth, 2010, 312, 2683-2688.	1.5	25
112	AlGaIn/GaN HEMTs on (001) Silicon Substrate With Power Density Performance of 2.9 W/mm at 10 GHz. IEEE Transactions on Electron Devices, 2010, 57, 1497-1503.	3.0	24
113	Deposited Thin SiO <sub>2</sub> for Gate Oxide on n-Type and p-Type GaN. Journal of the Electrochemical Society, 2010, 157, H1008.	2.9	20
114	Comparison of GaN-based MOS structures with different interfacial layer treatments. , 2010, , .		0
115	Enhanced terahertz transmission of GaN quantum wells. , 2010, , .		0
116	GaN transistor characteristics at elevated temperatures. Journal of Applied Physics, 2009, 106, .	2.5	67
117	Amplified piezoelectric transduction of nanoscale motion in gallium nitride electromechanical resonators. Applied Physics Letters, 2009, 94, .	3.3	110
118	The critical role of growth temperature on the structural and electrical properties of AlGaIn/GaN high electron mobility transistor heterostructures grown on Si(111). Journal of Applied Physics, 2009, 105, 033701.	2.5	50
119	Windowed growth of AlGaIn/GaN heterostructures on Silicon $\sim 111^\circ$ substrates for future MOS integration. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 371-374.	1.8	5
120	Luminescence and reflectivity characterization of AlGaIn/GaN high electron mobility transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S715.	0.8	1
121	Evaluation of SiN films for AlGaIn/GaN MIS-HEMTs on Si(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1016.	0.8	6
122	AlGaIn/GaN high electron mobility transistor grown by molecular beam epitaxy on Si(110): comparisons with Si(111) and Si(001). Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S1020.	0.8	13
123	Selective area growth of GaN-based structures by molecular beam epitaxy on micrometer and nanometer size patterns. Materials Science in Semiconductor Processing, 2009, 12, 16-20.	4.0	6
124	High temperature behaviour of AlGaIn/AlN/GaN Hall-FET sensors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 1-4.	3.5	9
125	Elaboration of (111) oriented 3C-SiC/Si layers for template application in nitride epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 9-14.	3.5	28
126	Strain engineering in GaN layers grown on silicon by molecular beam epitaxy: The critical role of growth temperature. Journal of Crystal Growth, 2009, 311, 2002-2005.	1.5	23



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127	Advances in quality and uniformity of (Al,Ga)N/GaN quantum wells grown by molecular beam epitaxy with plasma source. Journal of Crystal Growth, 2009, 311, 2029-2032.	1.5	7
128	Analysis of the C-V characteristic in SiO <sub>2</sub> /GaN MOS capacitors. , 2009, , .		0
129	Signature of monolayer and bilayer fluctuations in the width of (Al,Ga)N/GaN quantum wells. Physical Review B, 2009, 79, .	3.2	9
130	Preliminary results of bench implementation for the study of terahertz amplification in gallium nitride quantum wells. Journal of Physics: Conference Series, 2009, 193, 012094.	0.4	0
131	High temperature behaviour of GaN HEMT devices on Si(111) and sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1971-1973.	0.8	21
132	Realization of AlGaIn/GaN HEMTs on 3C-SiC/Si(111) substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1983-1985.	0.8	9
133	Subsurface Fe-doped semi-insulating GaN templates for inhibition of regrowth interface pollution in AlGaIn/GaN HEMT structures. Journal of Crystal Growth, 2008, 310, 948-954.	1.5	13
134	AlGaIn/GaN high electron mobility transistors grown on 3C-SiC/Si(111). Journal of Crystal Growth, 2008, 310, 4417-4423.	1.5	41
135	Composition analysis of semiconductor quantum wells by energy filtered convergent-beam electron diffraction. Ultramicroscopy, 2008, 108, 358-366.	1.9	6
136	Demonstration of AlGaIn/GaN High-Electron-Mobility Transistors Grown by Molecular Beam Epitaxy on Si(110). IEEE Electron Device Letters, 2008, 29, 1187-1189.	3.9	44
137	Growth of AlGaIn/GaN HEMTs on Silicon Substrates by MBE. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
138	Anomalous Hall Effect in Gd-implanted Wurtzite Al <sub>x</sub> Ga <sub>1-x</sub> N High Electron Mobility Transistor Structures. Materials Research Society Symposia Proceedings, 2008, 1111, 1.	0.1	1
139	Strain in 3C-SiC Heteroepitaxial Layers Grown on (100) and (111) Oriented Silicon Substrates. Materials Science Forum, 2008, 600-603, 207-210.	0.3	5
140	Growth of AlGaIn/GaN HEMTs on 3C-SiC/Si(111) Substrates. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	0
141	Investigation of AlGaIn <sup>+</sup> AlN <sup>+</sup> GaN heterostructures for magnetic sensor application from liquid helium temperature to 300°C. Applied Physics Letters, 2008, 92, .	3.3	16
142	Performance of Unstuck $\delta$ Gate AlGaIn/GaN HEMTs on (001) Silicon Substrate at 10 GHz. , 2008, , .		1
143	Magnetotransport in Gd-implanted wurtzite GaN <sup>+</sup> Al <sub>x</sub> Ga <sub>1-x</sub> N high electron mobility transistor structures. Applied Physics Letters, 2008, 92, 112111.	3.3	10
144	Thickness and substrate effects on AlN thin film growth at room temperature. EPJ Applied Physics, 2008, 43, 309-313.	0.7	34

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145	AlGaIn/GaN HEMTs on (001) oriented silicon substrate based on 100nm SiN recessed gate technology for low cost device fabrication. , 2007, , .		0
146	Development and analysis of low resistance ohmic contact to n-AlGaIn/GaN HEMT. Diamond and Related Materials, 2007, 16, 262-266.	3.9	29
147	In situ measurements of wafer bending curvature during growth of group-III-nitride layers on silicon by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 71-74.	1.5	18
148	Developments for the production of high-quality and high-uniformity AlGaIn/GaN heterostructures by ammonia MBE. Journal of Crystal Growth, 2007, 301-302, 434-436.	1.5	21
149	AlGaIn/GaN HEMTs regrown by MBE on epi-ready semi-insulating GaN-on-sapphire with inhibited interface contamination. Journal of Crystal Growth, 2007, 309, 1-7.	1.5	32
150	Realization of AlGaIn/GaN HEMTs on Si-on-polySiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2670-2673.	0.8	1
151	AlGaIn/GaN HEMTs on a (001)-Oriented Silicon Substrate Based on 100-nm SiN Recessed Gate Technology for Microwave Power Amplification. IEEE Transactions on Electron Devices, 2007, 54, 2843-2848.	3.0	13
152	Influence of crystal quality on electron mobility in AlGaIn/GaN HEMTs grown on Si(111), SiC and GaN templates. European Physical Journal Special Topics, 2006, 132, 365-368.	0.2	5
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154	Growth by molecular beam epitaxy of AlGaIn/GaN high electron mobility transistors on Si-on-polySiC. Superlattices and Microstructures, 2006, 40, 359-362.	3.1	3
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